L Number	Hits	Search Text	DB	Time stamp	
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			ЕРО; ЈРО;		
			DERWENT;		
		· ·	IBM_TDB		
7	73	,	USPAT;	2004/10/28 16:24	
		("0165636" "0017256" "0193899" "4957605" "5228280" "5240552" "5369	544S P34B4U37"	"5665214" "569581	0" " <i>5</i> 78702
8	1	5270530.pn.	USPAT;	2004/10/28 16:51	
•			US-PGPUB		
9	28	(USPAT;	2004/10/28 16:51	
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		and chamber\$4	,	·	
10	19	("5862054" "6074443" "6492281" "6618692" "6604012"	USPAT;	2004/10/28 17:17	
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			DERWENT;		
			IBM_TDB		
13	8760	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/10/28 22:06	
13	0/00	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	2004/10/20 22:00	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	ЕРО; ЛРО;		
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;		
				,	
		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB		
	1566	produc\$4 or manufactur\$3 or making)))	LIODAT	2004/10/20 20.50	
14	1766	118/719.ccls.	USPAT;	2004/10/28 20:50	
			US-PGPUB;		
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			DERWENT;		
			IBM_TDB		
15	358	427/9.ccls.	USPAT;	2004/10/28 20:50	
			US-PGPUB;		
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			DERWENT;		
			IBM_TDB		
16	2128	29/25.01.ccls.	USPAT;	2004/10/28 20:50	
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			ЕРО; ЈРО;		
			DERWENT;		
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17	3004	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT;	2004/10/28 20:50	
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			DERWENT;		
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17	2073011	IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	230 10/20 21.00	
		microelectronic or memory or (logic adj unit) or microprocessor or	EPO; ЛРО;		
		process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or	DERWENT;		
		etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or	IBM_TDB		
			TDIM_IDD		
		average or mean) near3 (time or rate)) or uniform\$3 or thickness or			
		(critical adj dimension\$3) or CD or variability or target or accura\$4 or		i	1
	1	defect\$5))	1	I	1

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20	1413512	((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:17
21	117771	(uniform\$3 or variability or capabilit\$4 or capacity)) (((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))) with (perform\$4 or quality or qualification or qualify\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:19
22	2902	((((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))) with (perform\$4 or quality or qualification or qualify\$3)) same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:19
23	73	((((process\$3 or cycle or defect\$4 or fail\$4 or fault\$4 or reject\$4) near3 (time or rate)) or ((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) near3 (uniform\$3 or variability or capabilit\$4 or capacity))).clm. with ((perform\$4 or quality or qualification or qualify\$3) with chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 21:59
24	14	((qualification or qualify\$3) with chamber).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:01
25	63	((qualification or qualify\$3) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:04
26	10	(((qualification or qualify\$3) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5)).clm.) and (chamber with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
27	2168	((qualification or qualif\$5 or qual) with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
28	894	((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:05
29	160	(((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or chamber))) and (chamber with (tool or equipment or fab or etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 22:06

30	44	((((qualification or qualif\$5 or qual) near3 (tool or equipment or fab or	USPAT,	2004/10/28 22:06
		etch\$3 or deposit\$7 or implant\$7 or planariz\$8 or polish\$5 or	US-PGPUB;	
		chamber))) and (chamber with (tool or equipment or fab or etch\$3 or	ЕРО; ЛРО;	
		deposit\$7 or implant\$7 or planariz\$8 or polish\$5))) and (118/719.ccls.	DERWENT,	
	Ì	or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	IBM TDB	
		700/19,49,52,99-104,108-111,119-121,123.ccls.)	_	